

Abstract

Process for etching a substrate

The invention relates to a process for etching at least one substrate (10), in particular at least one silicon wafer for the fabrication of DRAM memory chips, in which

- a) at least one substrate (10), for a first etching step (1), is arranged for a predetermined time in a first vessel containing a first etchant, then
- b) at least one substrate (10), for a first rinsing step (2), is arranged for a predetermined time in a second vessel containing a first rinsing agent, the first rinsing agent containing at least one wetting agent, and then
- c) at least one substrate (10), for a second etching step (3), is arranged for a predetermined time in a third vessel containing a second etchant.

Fig. 3

